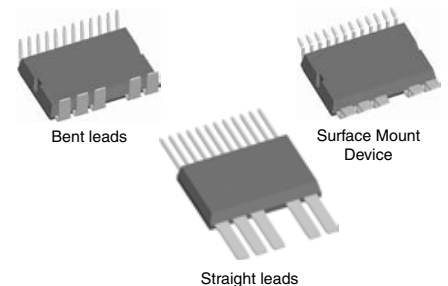
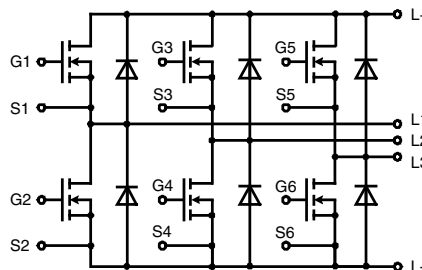


Three phase full Bridge

with Trench MOSFETs
in DCB isolated high current package

$V_{DSS} = 40 \text{ V}$
 $I_{D25} = 180 \text{ A}$
 $R_{DSon \text{ typ.}} = 2.0 \text{ m}\Omega$

Preliminary data



MOSFETs			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_{VJ} = 25^\circ\text{C to } 150^\circ\text{C}$	40	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	180	A
I_{D90}	$T_C = 90^\circ\text{C}$	138	A
I_{F25}	$T_C = 25^\circ\text{C (diode)}$	115	A
I_{F90}	$T_C = 90^\circ\text{C (diode)}$	75	A

Applications

- AC drives
- in automobiles
 - electric power steering
 - starter generator
 - in industrial vehicles
 - propulsion drives
 - fork lift drives
 - in battery supplied equipment

Features

- MOSFETs in trench technology:
 - low R_{DSon}
 - optimized intrinsic reverse diode
- package:
 - high level of integration
 - high current capability 300 A max.
 - aux. terminals for MOSFET control
 - terminals for soldering or welding connections
 - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings

Symbol	Conditions	Characteristic Values			
		$(T_{VJ} = 25^\circ\text{C, unless otherwise specified})$			
		min.	typ.	max.	
R_{DSon}	on chip level at $V_{GS} = 10 \text{ V}$		2.0	2.6	$\text{m}\Omega$
			3.2		$\text{m}\Omega$
$V_{GS(th)}$	$V_{DS} = 20 \text{ V}; I_D = 1 \text{ mA}$	2		4	V
I_{DSS}	$V_{DS} = V_{DSS}; V_{GS} = 0 \text{ V}$		0.1	1	μA
					mA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			0.2	μA
Q_g	$V_{GS} = 10 \text{ V}; V_{DS} = 14 \text{ V}; I_D = 25 \text{ A}$		94		nC
Q_{gs}			18		nC
Q_{gd}			29		nC
$t_{d(on)}$	$V_{GS} = 10 \text{ V}; V_{DS} = 30 \text{ V}$ $I_D = 25 \text{ A}; R_G = 10 \Omega$ inductive load		40		ns
t_r			85		ns
$t_{d(off)}$			140		ns
t_f			90		ns
E_{on}			tbd		mJ
E_{off}		tbd		mJ	
E_{recoff}		tbd		mJ	
R_{thJC}			1.3	1.0	K/W
R_{thJH}	with heat transfer paste (IXYS test setup)		1.3	1.6	K/W

Package options

- 3 lead forms available
 - straight leads (SL)
 - SMD lead version (SMD)
 - bent leads (BL)

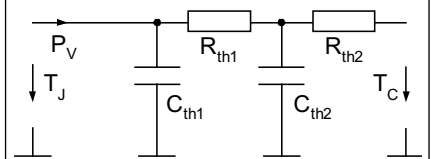
Source-Drain Diode

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
($T_J = 25^\circ\text{C}$, unless otherwise specified)					
V_{SD}	(diode) $I_F = 110\text{ A}$; $V_{GS} = 0\text{ V}$		1.0	1.6	V
t_{rr}	$I_F = 20\text{ A}$; $-di_F/dt = 100\text{ A}/\mu\text{s}$; $V_R = 20\text{ V}$		70		ns
Q_{RM}			tbd		μC
I_{RM}			tbd		A

Component

Symbol	Conditions	Maximum Ratings	
I_{RMS}	per pin in main current paths (P+, N-, L1, L2, L3) may be additionally limited by external connections	300	A
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{stg}		-55...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}$, 50/60 Hz, $f = 1\text{ minute}$	1000	V~
F_C	mounting force with clip	50 - 250	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin\ to\ chip}$	with heatsink compound		0.6	$\text{m}\Omega$
C_p	coupling capacity between shorted pins and mounting tab in the case		160	pF
Weight	typ.		25	g

Equivalent Circuits for Simulation
Thermal Response


junction - case (typ.)

$$C_{th1} = \text{tbd J/K}; R_{th1} = \text{tbd K/W}$$

$$C_{th2} = \text{tbd J/K}; R_{th2} = \text{tbd K/W}$$

